



PTO/SB/08A (05-03)

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Substitute for form 1449A/PTO				Complete if Known	
				Application Number	10/667,871
INFORMATION DISCLOSURE STATEMENT BY APPLICANT (use as many sheets as necessary)				Filing Date	September 22, 2003
				First Named Inventor	Yeo, et al.
				Art Unit	2811
				Examiner Name	Unknown
Sheet	1	of	2	Attorney Docket Number	TSM03-0553

U.S. PATENT DOCUMENTS					
Examiner Initials*	Cite No. ¹	Document Number	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
		Number - Kind Code ² (if known)			
9/11	A	US-4,314,269	02-02-1982	Fujiki	
9/11	B	US-5,629,544	05-13-1997	Voldman, et al.	
9/11	C	US-5,811,857	09-22-1998	Assaderaght, et al.	
9/11	D	US-6,008,095	12-28-1999	Gardner, et al.	
9/11	E	US-6,015,993	01-18-2000	Voldman, et al.	
9/11	F	US-6,232,163 B1	05-15-2001	Voldman, et al.	
9/11	G	US-6,258,664 B1	07-10-2001	Reinberg	
9/11	H	US-6,294,834 B1	09-25-2001	Yeh, et al.	
9/11	I	US-6,358,791 B1	03-19-2002	Hsu, et al.	
9/11	J	US-2002/0153549 A1	10-24-2002	Laibowitz, et al.	
9/11	K	US-6,475,838 B1	11-05-2002	Bryant, et al.	
9/11	L	US-6,489,664 B2	12-03-2002	Re, et al.	
9/11	M	US-2003/0030091 A1	02-13-2003	Bulsara, et al.	
9/11	N	US-6,524,905 B2	02-25-2003	Yamamichi, et al.	
9/11	O	US-2003/0080386 A1	05-01-2003	Ker, et al.	
9/11	P	US-6,558,998 B2	05-06-2003	Belleville, et al.	

FOREIGN PATENT DOCUMENTS							
Examiner Initials*	Cite No. ¹	Foreign Patent Document		Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear	T ⁶
		Country Code ³ - Number ⁴ - Kind Code ⁵ (if known)					
9/1	Q	WO 03/017336 A2		02-27-2003	Amberwave Systems Corporation		

OTHER PRIOR ART - NON PATENT LITERATURE DOCUMENTS			
Examiner Initials*	Cite No.	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T ²
9/11	R	WANG, L.K., et al., "On-Chip Decoupling Capacitor Design to Reduce Switching-Noise-Induced Instability in CMOS/SOI VLSI," Proceedings of the 1995 IEEE International SOI Conference, Oct. 1995, pp.100-101.	
9/11	S	YEOH, J.C., et al., "MOS Gated Si:SiGe Quantum Wells Formed by Anodic Oxidation," Semicond. Sci. Technol. (1998), Vol. 13, pp. 1442-1445, IOP Publishing Ltd., UK.	
9/11	T	CAVASSILAS, N., et al., "Capacitance-Voltage Characteristics of Metal-Oxide-Strained Semiconductor Si/SiGe Heterostructures," Nanotech 2002, Vol. 1, pp. 600-603.	

Examiner Signature	<i>James M. Kennedy</i>	Date Considered	4 March 3, 2005
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Substitute for form 1449B/PTO

**INFORMATION DISCLOSURE
STATEMENT BY APPLICANT**
(use as many sheets as necessary)

Sheet

2

of

2

Complete if Known

Application Number

10/667.871

Filing Date

September 22, 2003

First Named Inventor

Yeo, et al.

Group Art Unit

2811

Examiner Name

Unknown

Attorney Docket Number

TSM03-0553

OTHER PRIOR ART -- NON PATENT LITERATURE DOCUMENTS

Examiner Signature	<i>James M. Kennedy</i>	Date Considered	
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Substitute for form 1449B/PTO		Complete if Known	
INFORMATION DISCLOSURE STATEMENT BY APPLICANT (use as many sheets as necessary)		Application Number	10/667,871
		Filing Date	September 22, 2003
		First Named Inventor	Yeo, et al.
		Group Art Unit	2811
		Examiner Name	TBD
		Attorney Docket Number	TSM03-0553
Sheet	2	of	3

OTHER PRIOR ART – NON PATENT LITERATURE DOCUMENTS			
Examiner Initials*	Cite No.	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T ²
JU	23	ISMAIL, K., et al., "Electron Transport Properties of Si/SiGe Heterostructures: Measurements and Device Implications," Applied Physics Letters, Vol. 63, No. 5, (August 2, 1993), pp. 660-662.	
JU	24	NAYAK, D.K., et al., "Enhancement-Mode Quantum-Well Ge _x Si _{1-x} PMOS," IEEE Electron Device Letters, Vol. 12, No. 4, (April 1991), pp. 154-156.	
JU	25	GAMIZ, F., et al., "Strained-Si/SiGe-on-Insulator Inversion Layers: The Role of Strained-Si Layer Thickness on Electron Mobility," Applied Physics Letters, Vol. 80, No. 22, (June 3, 2002), pp. 4160-4162.	
JU	26	GAMIZ, F., et al., "Electron Transport in Strained Si Inversion Layers Grown on SiGe-on-Insulator Substrates," Journal of Applied Physics, Vol. 92, No. 1, (July 1, 2002), pp. 288-295.	
JU	27	MIZUNO, T., et al., "Novel SOI p-Channel MOSFETs With Higher Strain in Si Channel Using Double SiGe Heterostructures," IEEE Transactions on Electron Devices, Vol. 49, No. 1, (January 2002), pp. 7-14.	
JU	28	TEZUKA, T., et al., "High-Performance Strained Si-on-Insulator MOSFETs by Novel Fabrication Processes Utilizing Ge-Condensation Technique," Symposium On VLSI Technology Digest of Technical Papers, (2002), pp. 96-97.	
JU	29	JURCZAK, M., et al., "Silicon-on-Nothing (SON) – an Innovative Process for Advanced CMOS," IEEE Transactions on Electron Devices, Vol. 47, No. 11, (November 2000), pp. 2179-2187.	
JU	30	JURCZAK, M., et al., "SON (Silicon on Nothing) – A NEW DEVICE ARCHITECTURE FOR THE ULSI ERA," Symposium on VLSI Technology Digest of Technical Papers, (1999), pp. 29-30.	
JU	31	MAITI, C.K., et al., "Film Growth and Material Parameters," Application of Silicon-Germanium Heterostructure, Institute of Physics Publishing, Ch. 2 (2001) pp. 32-42.	
JU	32	TIWARI, S., et al., "Hole Mobility Improvement in Silicon-on-Insulator and Bulk Silicon Transistors Using Local Strain," International Electron Device Meeting, (1997), pp. 939-941.	
JU	33	OOTSUKA, F., et al., "A Highly Dense, High-Performance 130nm Node CMOS Technology for Large Scale System-on-a-Chip Applications," International Electron Device Meeting, (2000), pp. 575-578.	
JU	34	MATTHEWS, J.W., et al., "Defects in Epitaxial Multilayers – I. Misfit Dislocations," Journal of Crystal Growth, Vol. 27, (1974), pp. 118-125.	
JU	35	MATTHEWS, J.W., et al., "Defects in Epitaxial Multilayers – II. Dislocation Pile-Ups, Threading Dislocations, Slip Lines and Cracks," Journal of Crystal Growth, Vol. 29, (1975), pp. 273-280.	
Examiner Signature	[Signature]		Date Considered March 2, 2005

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INFORMATION DISCLOSURE STATEMENT BY APPLICANT <i>(use as many sheets as necessary)</i>		Application Number	10/667,871
		Filing Date	September 22, 2003
		First Named Inventor	Yeo, <i>et al.</i>
		Group Art Unit	2811
		Examiner Name	TBD
		Attorney Docket Number	TSM03-0553
Sheet	3	of	3

OTHER PRIOR ART – NON PATENT LITERATURE DOCUMENTS			
Examiner Initials*	Cite No.	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	2
JU	36	MATTHEWS, J.W., <i>et al.</i> , "Defects in Epitaxial Multilayers – III. Preparation of Almost Perfect Multilayers," Journal of Crystal Growth, Vol. 32, (1976), pp. 265-273.	
JU	37	SCHÜPPEN, A., <i>et al.</i> , "Mesa and Planar SiGe-HBTs on MBE-Wafers," Journal of Materials Science: Materials in Electronics, Vol. 6, (1995), pp. 298-305.	
JU	38	MATTHEWS, J.W., "Defects Associated with the Accommodation of Misfit Between Crystals," J. Vac. Sci. Technol., Vol. 12, No. 1 (Jan./Feb. 1975), pp. 126-133.	
JU	39	HUANG, X., <i>et al.</i> , "Sub-50 nm P-Channel FinFET," IEEE Transactions on Electron Devices, Vol. 48, No. 5, May 2001, pp. 880-886.	
JU	40	SHAHIDI, G.G., "SOI Technology for the GHz Era," IBM J. Res. & Dev., Vol. 46, No. 2/3, March/May 2002, pp. 121-131.	
JU	41	SHIMIZU, A., <i>et al.</i> , "Local Mechanical Stress Control (LMC): A New Technique for CMOS-Performance Enhancement," IEDM 2001, pp. 433-436.	
JU	42	WONG, H.-S.P., "Beyond the Conventional Transistor," IBM J. Res. & Dev., Vol. 46, No. 2/3, March/May 2002, pp. 133-167.	
JU	43	YANG, F.L., <i>et al.</i> , "25 nm CMOS Omega FETs," IEDM 2002, pp. 255-258.	
JU	44	YANG, F.L., <i>et al.</i> , "35nm CMOS FinFETs," 2002 Symposium on VLSI Technology Digest of Technical Papers, 2002, pp. 104-105.	
JU	45	THOMPSON, S., <i>et al.</i> , "A 90 nm Logic Technology Featuring 50nm Strained Silicon Channel Transistors, 7 Layers of Cu Interconnects, Low k ILD, and 1 um ² SRAM Cell," IEDM, pp. 61-64.	
JU	46	WELSER, J., <i>et al.</i> , "NMOS and PMOS Transistors Fabricated in Strained Silicon/Relaxed Silicon-Germanium Structures," IEDM 1992, pp. 1000-1002.	

Examiner Signature	<i>Quinn M. Kennedy</i>	Date Considered	March 2, 2005
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JH	1	US- 2004/0026765 A1	02-12-2004	Currie, et al.	
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FOREIGN PATENT DOCUMENTS						
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Examiner Signature	<i>James M. Kennedy</i>	Date Considered	March 2, 2005
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